501.42645VX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	S. SHUKURI
Application No.:	Rule 1.53(b) Divisional of U.S. Patent Application Serial No. 10/400,469, filed March 28, 2003
Filed:	On Even Date Herewith
For:	SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AN A METHOD OF MANUFACTURING THE SAME
Art Group of Parent:	2818
Examiner of Parent:	Unknown

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §1.97 & 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

January 30, 2004

Sir:

In the matter of the above-identified application, this Information Disclosure Statement is being submitted with the following citation as specified in 37 CFR §1.97(d).

> "A copy of any patent, publication or other information listed in an Information Disclosure Statement is not required to be provided if it was previously cited by or submitted to the Office in a prior application, provided that the prior application is properly identified in the statement and relied upon for an earlier filing date under 35 U.S.C. §120."

Applicants are submitting herewith a copy of Form PTO/SB/08A which list documents cited in parent application Serial No. 10/400,469, filed March 28, 2003, the entire disclosure of which is hereby incorporated by reference.

It is respectfully requested that this information disclosure statement be considered by the Examiner.

To the extent necessary, the applicants petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the deposit account of Antonelli, Terry, Stout & Kraus, LLP Deposit Account No. 01-2135 (Docket No. 501.42645VX1).

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP

By 

Gregory E. Montone
Reg. No. 28,141

GEM/dlt

1300 North Seventeenth Street, Suite 1800
Arlington, Virginia 22209
Telephone: (703) 312-6600
Facsimile: (703) 312-6666

PTO/SB/08A (10-01)
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Compl te if Known	
Application Number	Not assigned yet
Filing Date	On even date herewith
First Named Inventor	S. SHUKURI
Art Unit	Not assigned yet
Examiner Name	Not assigned yet
Attorney Docket Number	501.42645VX1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		5,768,192		6/16/98	Eitan	
		5,966,603		10/12/99	Eitan	
		6,011,725		1/4/00	Eitan	
		6,180,538		1/30/01	Hallival et al.	
		5,408,115		4/18/95	Chang	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]–Number[4]–Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

OTHER PRIOR ART—NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
		"Can NROM, a 2 Bit, Trapping Storage NVM Cell, Give a Real Challenge to Floating Gate Cells?" Eitan et al., Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, Tokyo, 1999, pp.522-524	
		"High Speed Program/Erase Sub 100 nm MONOS Memory Cell" Fujiwara et al., pp.75-77	
		"A Novel Flash Memory Device with Split Gate Source Side Injection and ONO Charge Storage Stack (SPIN)" Chen et al., 1997 Symposium on VLSI Technology Digest of Technical Papers, pp. 63-64	
		"Twin MONOS Cell with Dual Control Gates" Hayashi et al., Symposium on VLSI Technology Digest of Technical Papers, pp. 122-123	

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Applicant's unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard St.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.